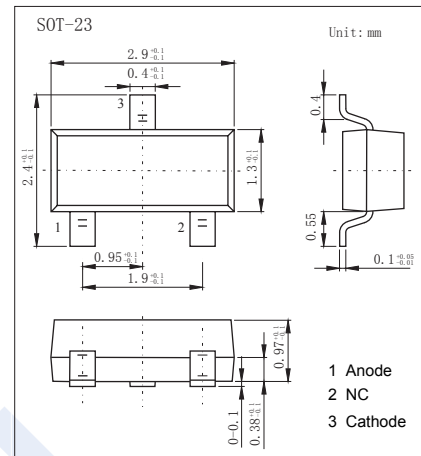
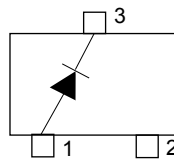


## Switching Diodes

## HSM83 (KSM83)

## ■ Features

- High reverse voltage. ( $V_R = 250V$ )
- Silicon Epitaxial Planar Diode for High Voltage Switching

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	$V_{RM}$	300	V
DC Blocking Voltage	$V_R$	250	
Average Rectified Output Current	$I_o$	100	mA
Peak Forward Surge Current	$I_{FM}$	300	
Non-Repetitive Peak Forward Surge Current (Note.1)	$I_{FSM}$	2	A
Junction Temperature	$T_J$	125	$^\circ\text{C}$
Storage Temperature range	$T_{stg}$	-55 to 125	

Note.1: Value at duration of 10msec.

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	$V_R$	$I_R = 100 \mu\text{A}$	300			V
Forward voltage	$V_F$	$I_F = 100 \text{mA}$			1.2	
Reverse voltage leakage current	$I_{R1}$	$V_R = 250 \text{V}$			0.2	$\mu\text{A}$
	$I_{R2}$	$V_R = 300 \text{V}$			100	
Capacitance between terminals	$C_T$	$V_R = 0 \text{V}, f = 1 \text{MHz}$		1.5	3	pF
Reverse recovery time	$t_{rr}$	$I_F = I_R = 30 \text{mA}, I_{rr} = 3 \text{mA}, R_L = 100 \Omega$			100	ns

## ■ Marking

Marking	F7
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## Switching Diodes

## HSM83 (KSM83)

## ■ Typical Characteristics

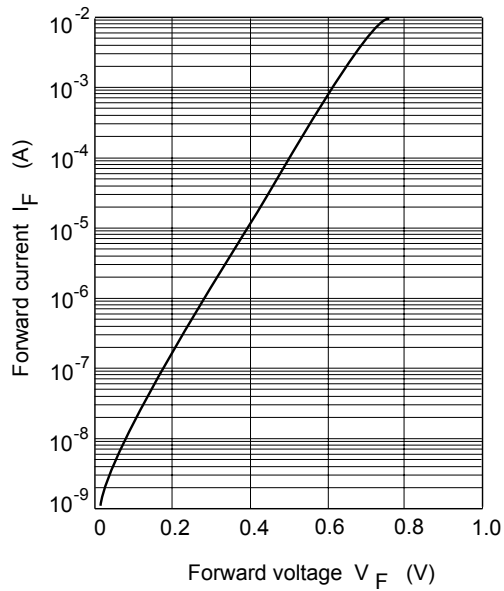


Fig.1 Forward current Vs. Forward voltage

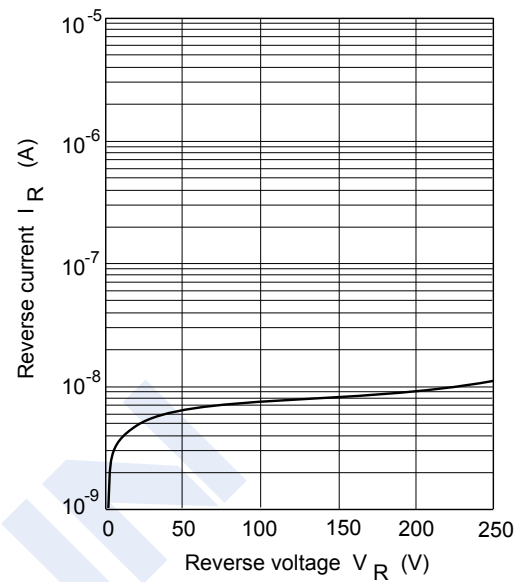


Fig.2 Reverse current Vs. Reverse voltage

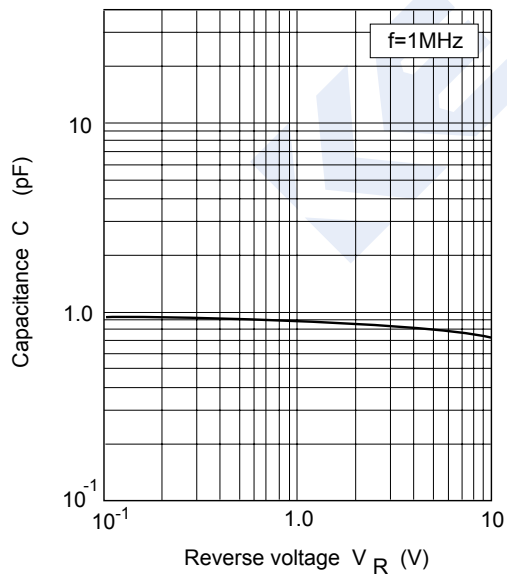


Fig.3 Capacitance Vs. Reverse voltage